

INFORMATION DISCLOSURE CITATION
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Docket Number (Optional)

TWI-11220

Application Number

10/691,132

Applicant(s)

Jon Opsal et al.

Filing Date

October 22, 2003

Group Art Unit

Unknown 2877

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
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	AU	WO 00/68656	11/16/2000	PCT	G01J	4/00		

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	AV	M. Fried et al., "Nondestructive determination of damage depth profiles in ion-implanted semiconductors by spectroscopic ellipsometry using different optical models," <i>J. Appl. Phys.</i> , Vol. 71, No. 6, 15 March 1992, pp. 2835-2843.
	AW	A.P. Webb et al., "Refractive index profiles induced by ion implantation into silica," <i>J. Phys. D: Appl. Phys.</i> , Vol. 9, 1976, pp. 1343-1354.
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	BA	X-F. He et al., "Disorder effects on optical spectra and band structure of Si induced by ion implantation," <i>J. Appl. Phys.</i> , Vol. 66, No. 11, 1 December 1989, pp. 5261-5266.
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	BC	Kravetsky, Kulyuk et al., "Reflected optical second harmonic generation as a method for characterization of ion-implanted, thermal annealed silicon surfaces and silicon-insulator interfaces," <i>Ion Implanted Technology</i> , Vol. 94, 1995, pp. 656-659.
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Examiner

Date Considered

19 JAN. 2005

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	BL	L. Chen et al., "Transient photomodulation spectroscopy of nanocrystalline hydrogenated silicon," <i>Physical Review B</i> , Vol. 39, No. 8, 15 March 1989, pp. 5121-5127.
	BM	A.H.M. Holtslag et al., "Noble-gas ion bombardment on clean silicon surfaces," <i>Physical Review B</i> , Vol. 38, No. 15, 15 November 1988, pp. 10556-10570.
	BN	R.E. Hummel et al., "Optical investigations of ion implant damage in silicon," <i>J. Appl. Phys.</i> , Vol. 63, No. 8, 15 April 1988, pp. 2591-2594.
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	BP	J. Narayan et al., "Formation and nondestructive characterization of ion implanted silicon-on-insulator layers," <i>Appl. Phys. Lett.</i> , Vol. 51, No. 5, 3 August 1987, pp. 343-345.
	BQ	P.J. McMarr et al., "Spectroscopic ellipsometry: A new tool for nondestructive depth profiling and characterization of interfaces," <i>J. Appl. Phys.</i> , Vol. 59, No. 3, 1 February 1986, pp. 694-701.
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	BS	R.W. Collins et al., "A ellipsometry study of a hydrogenated amorphous silicon based n-i structure," <i>J. Appl. Phys.</i> , Vol. 57, No. 10, 15 May 1985, pp. 4566-4571.
	BT	K. Vedam et al., "Nondestructive depth profiling by spectroscopic ellipsometry," <i>Appl. Phys. Lett.</i> , Vol. 47, No. 4, 15 August 1985, pp. 339-341.
	BU	M. Erman et al., "Analysis of ion-implanted GaAs by Spectroscopic ellipsometry," <i>Surface Science</i> , Vol. 135, 1983, pp. 353-373.
	BV	J.B. Theeten et al., "Depth profiling and interface analysis using spectroscopic ellipsometry," <i>J. Vac. Sci. Technol.</i> , Vol. 20, No. 3, March 1982, pp. 471-475.
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	BY	Q. Kim & Y.S. Park, "Ellipsometric investigation of ion-implanted GaAs," <i>Surface Science</i> , Vol. 96, 1980, pp. 307-318.
	BZ	Q. Kim et al., "Characterization of ion-implanted GaAs by ellipsometry," <i>J. Appl. Phys.</i> , Vol. 51, No. 4, April 1980, pp. 2024-2029.
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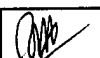




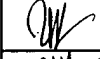
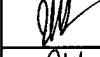
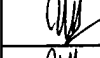

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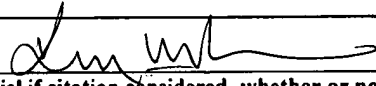
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	CG	A. Rosencwaig et al., "Thermal wave characterization of semiconductors and superconductors," <i>Review of Progress in Quantitative Nondestructive Evaluation</i> , Vol 8B, 1989, pp. 1195-1201.
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	CI	J. Bailey et al., "Subsurface defects in silicon investigated by modulated optical reflectance measurements," <i>Review of Progress in Quantitative Nondestructive Evaluation</i> , Vol 8B, 1989, pp. 1263-1271.
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